#### **NSS30070MR6T1G**

## 30 V, 0.7 A, Low V<sub>CE(sat)</sub> PNP Transistor

ON Semiconductor's  $e^2$ PowerEdge family of low  $V_{CE(sat)}$  transistors are miniature surface mount devices featuring ultra low saturation voltage ( $V_{CE(sat)}$ ) and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Typical application are DC–DC converters and power management in portable and battery powered products such as cellular and cordless phones, PDAs, computers, printers, digital cameras and MP3 players. Other applications are low voltage motor controls in mass storage products such as disc drives and tape drives. In the automotive industry they can be used in air bag deployment and in the instrument cluster. The high current gain allows e<sup>2</sup>PowerEdge devices to be driven directly from PMU's control outputs, and the Linear Gain (Beta) makes them ideal components in analog amplifiers.

#### **Features**

• This Device is Pb-Free and is RoHS Compliant

#### MAXIMUM RATINGS (T<sub>C</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V <sub>CEO</sub>	30	V
Collector-Base Voltage	V <sub>CBO</sub>	40	V
Emitter-Base Voltage	V <sub>EBO</sub>	5.0	V
Collector Current	I <sub>C</sub>	700	mA
Base Current	I <sub>B</sub>	350	mA
Total Power Dissipation @ $T_C$ = 25°C Total Power Dissipation @ $T_C$ = 85°C Thermal Resistance – Junction-to-Ambient (Note 1)	P <sub>D</sub> P <sub>D</sub> R <sub>θJA</sub>	342 178 366	mW mW °C/W
Total Power Dissipation @ $T_C = 25^{\circ}C$ Total Power Dissipation @ $T_C = 85^{\circ}C$ Thermal Resistance – Junction-to-Ambient (Note 2)	P <sub>D</sub> P <sub>D</sub> R <sub>θJA</sub>	665 346 188	mW mW °C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	ç

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

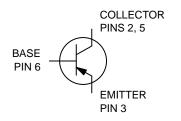
- 1. Minimum FR-4 or G-10 PCB, Operating to Steady State.
- Mounted onto a 2" square FR-4 Board (1" sq. 2 oz Cu 0.06" thick single sided), Operating to Steady State.



#### ON Semiconductor®

http://onsemi.com

# $\begin{array}{c} 30 \text{ VOLTS} \\ 0.7 \text{ AMPS} \\ \text{PNP LOW V}_{\text{CE(sat)}} \text{ TRANSISTOR} \\ \text{EQUIVALENT R}_{\text{DS(on)}} \text{ 320 m} \Omega \end{array}$





SC-74 CASE 318F STYLE 2

#### **DEVICE MARKING**



VS2 = Specific Device Code

M = Date Code

= Pb–Free Package

(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NSS30070MR6T1G	SC-74 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

#### **NSS30070MR6T1G**

#### **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic			Min	Тур	Max	Unit	
OFF CHARACTERISTICS							
Collector - Base Breakdown Voltage	$(I_C = 100 \mu A)$	V <sub>(BR)CBO</sub>	40	_	_	V	
Collector - Emitter Breakdown Voltage	$(I_C = 10 \text{ mA})$	V <sub>(BR)CEO</sub>	30	_	-	V	
Emitter-Base Breakdown Voltage	(I <sub>E</sub> = 100 μA)	V <sub>(BR)EBO</sub>	5.0	_	-	V	
Collector Cutoff Current (V <sub>C</sub>	$(V_{CB} = 25 \text{ V}, I_E = 0 \text{ A})$ B = 25 V, $I_E = 0 \text{ A}, T_A = 125^{\circ}\text{C})$	Ісво	- -	- -	1.0 10	μΑ	
Emitter Cutoff Current	$(V_{EB} = 5.0 \text{ V}, I_{C} = 0 \text{ A})$	I <sub>EBO</sub>	_	_	10	μΑ	
ON CHARACTERISTICS							
DC Current Gain	$(V_{CE} = 3.0 \text{ V}, I_{C} = 100 \text{ mA})$	h <sub>FE</sub>	150	-	-	V	
Collector - Emitter Saturation Voltage	$(I_C = 500 \text{ mA}, I_B = 50 \text{ mA})$	V <sub>CE(sat)</sub>	-	-	0.25	V	
Collector - Emitter Saturation Voltage	$(I_C = 700 \text{ mA}, I_B = 70 \text{ mA})$	V <sub>CE(sat)</sub>	-	-	0.4	V	
Base-Emitter Saturation Voltage	$(I_C = 700 \text{ mA}, I_B = 70 \text{ mA})$	V <sub>BE(sat)</sub>	-	-	1.1	V	
Base-Emitter Turn-On Voltage	$(I_C = 700 \text{ mA}, V_{CE} = 1.0 \text{ V})$	V <sub>BE(on)</sub>	_	-	1.0	V	

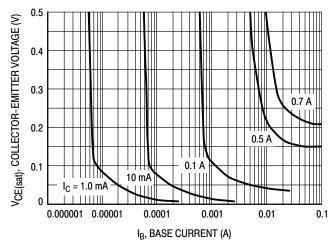
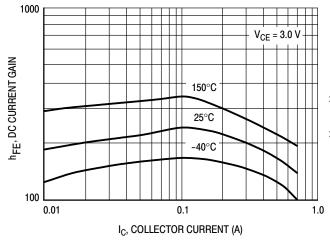
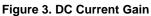


Figure 1. Collector Saturation Region

Figure 2. Collector Saturation Region





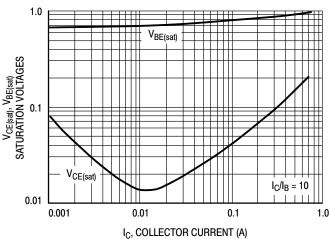


Figure 4. "SAT" Voltages

#### **NSS30070MR6T1G**

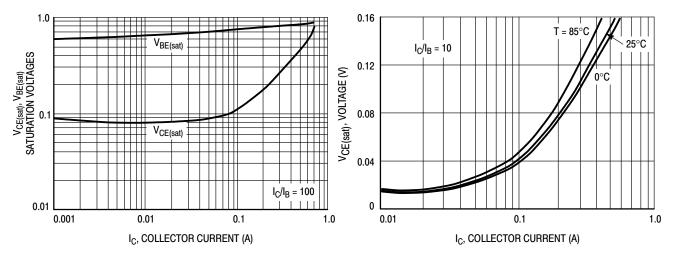


Figure 5. "SAT" Voltages

Figure 6. Collector-Emitter Saturation Voltage

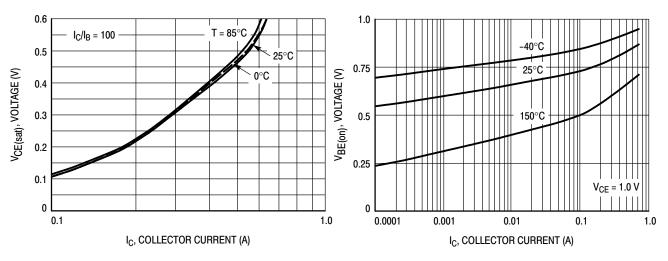


Figure 7. Collector-Emitter Saturation Voltage

Figure 8.  $V_{BE(on)}$  Voltage

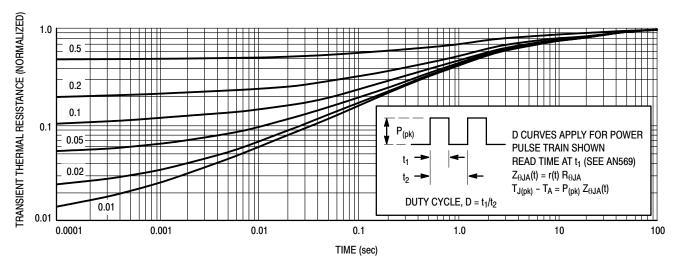


Figure 9. Thermal Response Curve





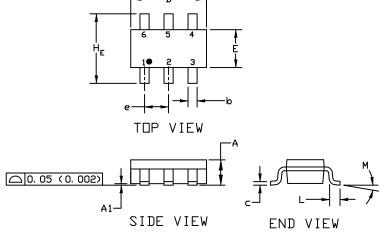
SC-74 CASE 318F ISSUE P

**DATE 07 OCT 2021** 

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994
- 2. CONTROLLING DIMENSION: INCHES
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.

	MI	LLIMETER	25	INCHES		
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0. 90	1. 00	1. 10	0. 035	0. 039	0. 043
A1	0. 01	0. 06	0.10	0. 001	0. 002	0. 004
b	0. 25	0. 37	0. 50	0. 010	0. 015	0. 020
c	0.10	0. 18	0. 26	0. 004	0. 007	0. 010
D	2. 90	3. 00	3. 10	0. 114	0. 118	0. 122
Ε	1. 30	1. 50	1. 70	0. 051	0. 059	0. 067
е	0. 85	0. 95	1. 05	0. 034	0. 037	0. 041
HE	2. 50	2. 75	3. 00	0. 099	0. 108	0. 118
L	0. 20	0, 40	0. 60	0, 008	0. 016	0, 024
М	0*		10*	0*		10*



### GENERIC MARKING DIAGRAM\*



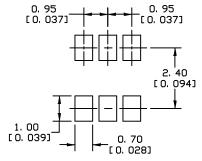
XXX = Specific Device Code

M = Date Code

= Pb-Free Package
 (Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may

not follow the Generic Marking.



For additional information on our Pb-Free strategy and soldering details, please download the UN Semiconductor Soldering and Mounting Techniques Reference Manual, SULDERRM/D.

SOLDERING FOOTPRINT

STYLE 1: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. ANODE 6. CATHODE	STYLE 2: PIN 1. NO CONNECTION 2. COLLECTOR 3. EMITTER 4. NO CONNECTION 5. COLLECTOR 6. BASE	STYLE 3: PIN 1. EMITTER 1 2. BASE 1 3. COLLECTOR 2 4. EMITTER 2 5. BASE 2 6. COLLECTOR 1	STYLE 4: PIN 1. COLLECTOR 2 2. EMITTER 1/EMITTER 2 3. COLLECTOR 1 4. EMITTER 3 5. BASE 1/BASE 2/COLLECTOR 3 6. BASE 3	STYLE 5: PIN 1. CHANNEL 1 2. ANODE 3. CHANNEL 2 4. CHANNEL 3 5. CATHODE 6. CHANNEL 4	STYLE 6: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE
STYLE 7: PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1	STYLE 8: PIN 1. EMITTER 1 2. BASE 2 3. COLLECTOR 2 4. EMITTER 2 5. BASE 1 6. COLLECTOR 1	STYLE 9: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 10: PIN 1. ANODE/CATHODE 2. BASE 3. EMITTER 4. COLLECTOR 5. ANODE 6. CATHODE	STYLE 11: PIN 1. EMITTER 2. BASE 3. ANODE/CATHOD 4. ANODE 5. CATHODE 6. COLLECTOR	DE

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